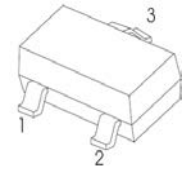
SWITCHING DIODE



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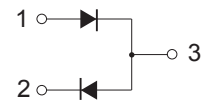
FEATURES

CMSD2004S type is a silicon switching dual in series diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability. Power dissipation

MARKING : B6D



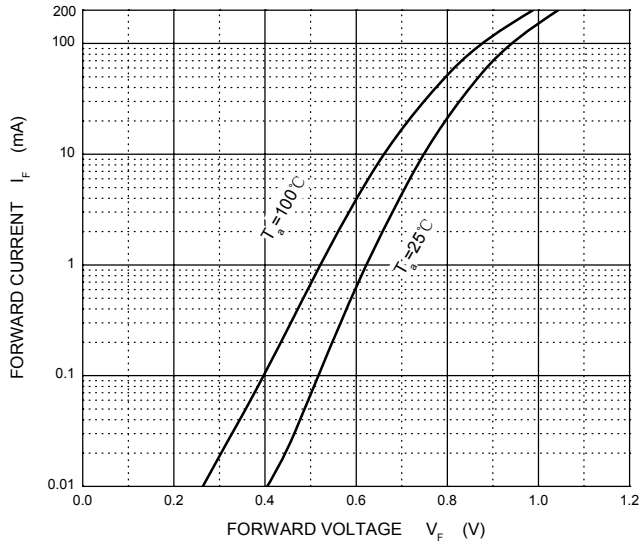
Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	300	V
DC Blocking Voltage	V_R	240	V
Average Rectified Output Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.5	A
Power Dissipation	P_D	250	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	500	℃/W
Operation Junction and Storage Temperature Range	T_J,T_{STG}	-55~+150	℃

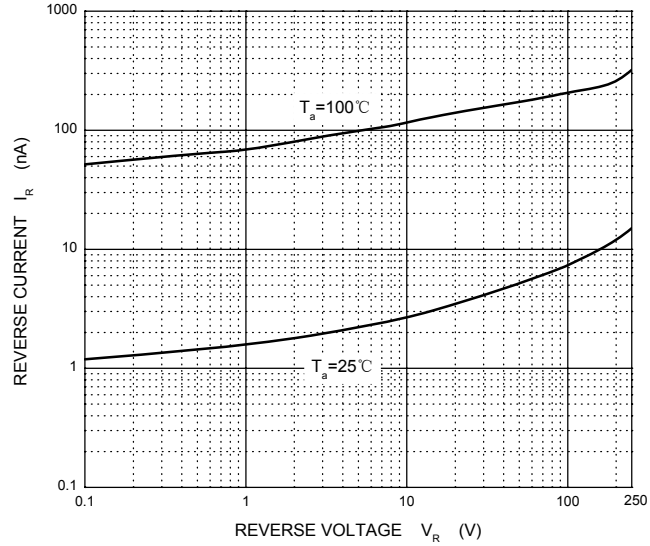
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	240		V
Reverse voltage leakage current	I_R	V_R=240V		0.1	μA
Forward voltage	V_F	I_F=100mA		1	V
Diode capacitance	C_D	V_R=0V f=1MHz		5	pF
Reveres recovery time	t_{rr}	I_F=I_R=30mA,R_L=100Ω		50	ns

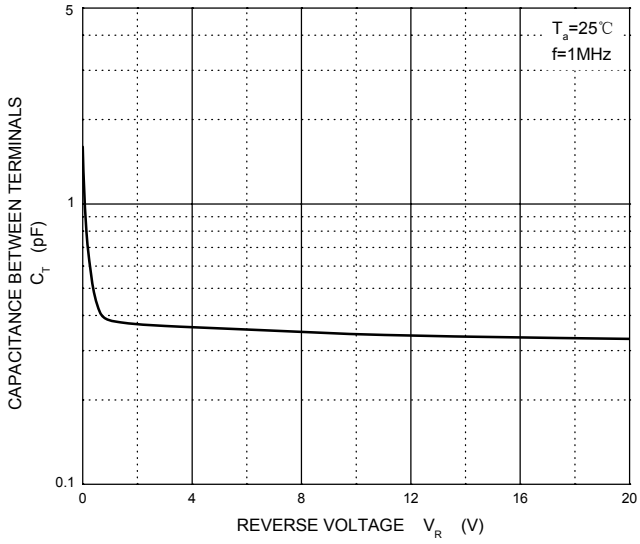
Forward Characteristics



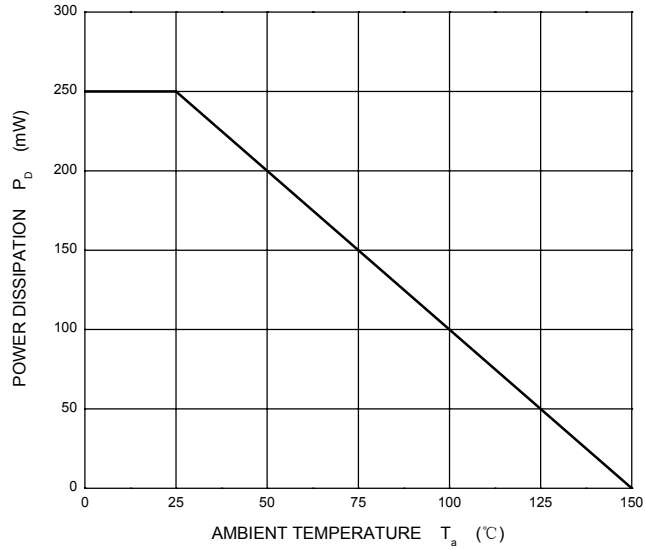
Reverse Characteristics



Capacitance Characteristics Per Diode



Power Derating Curve



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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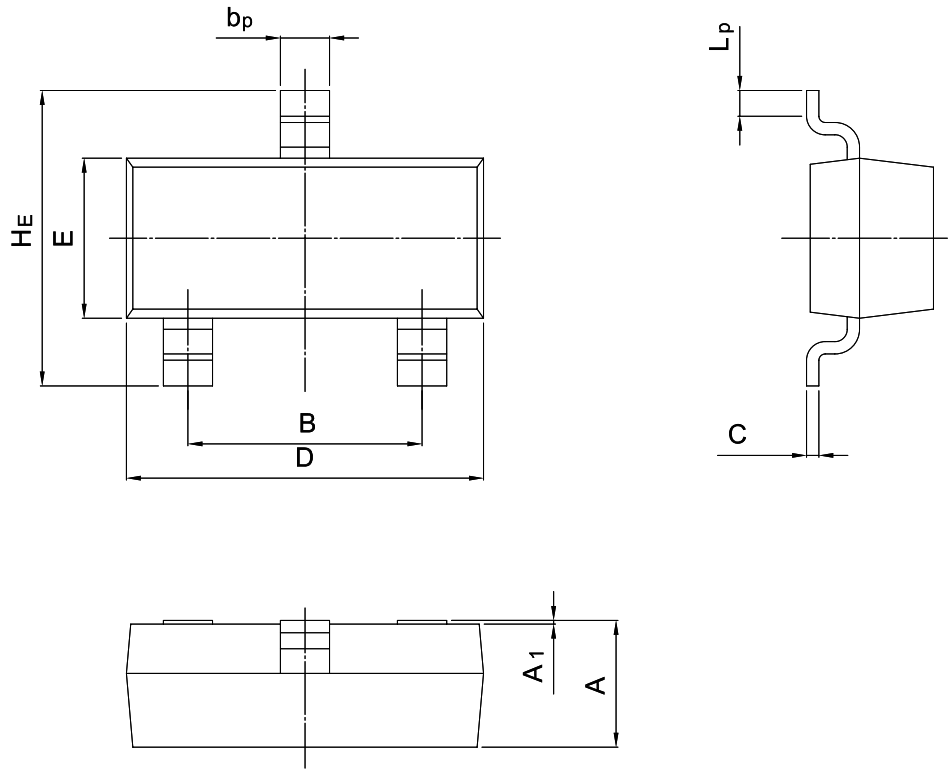

UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20